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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/581,410	06/01/2006	Daisuke Kumaki	0553-0504	3756
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SUITE 2850			BOWMAN, MARY ELLEN	
200 WEST ADAMS STREET CHICAGO, IL 60606			ART UNIT	PAPER NUMBER
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)
	10/581,410	KUMAKI ET AL.
Office Action Summary	Examiner	Art Unit
	MARY ELLEN BOWMAN	2879
The MAILING DATE of this communication ap Period for Reply	ppears on the cover sheet with the	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPUBLICHEVER IS LONGER, FROM THE MAILING IF Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory perior Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATIO 1.136(a). In no event, however, may a reply be tild d will apply and will expire SIX (6) MONTHS from the, cause the application to become ABANDONE	N. mely filed the mailing date of this communication. ED (35 U.S.C. § 133).
Status		
Responsive to communication(s) filed on <u>05.</u> This action is FINAL . 2b) ☐ The 3) ☐ Since this application is in condition for allow closed in accordance with the practice under	is action is non-final. ance except for formal matters, pr	
Disposition of Claims		
4) Claim(s) 9-20 and 32-47 is/are pending in the 4a) Of the above claim(s) is/are withdrest 5) Claim(s) is/are allowed. 6) Claim(s) 9-20 and 32-47 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/	awn from consideration. /or election requirement.	
 9) The specification is objected to by the Examir 10) The drawing(s) filed on is/are: a) ac Applicant may not request that any objection to the Replacement drawing sheet(s) including the corre 11) The oath or declaration is objected to by the E 	ecepted or b) objected to by the e drawing(s) be held in abeyance. Se ection is required if the drawing(s) is ob	e 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bure. * See the attached detailed Office action for a list	nts have been received. nts have been received in Applicat fority documents have been receiv au (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal I 6) Other:	ate

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on August 5, 2009 has been entered.

Response to Arguments

Applicant's arguments with respect to claims 9-20 and 32-47 have been considered but are most in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

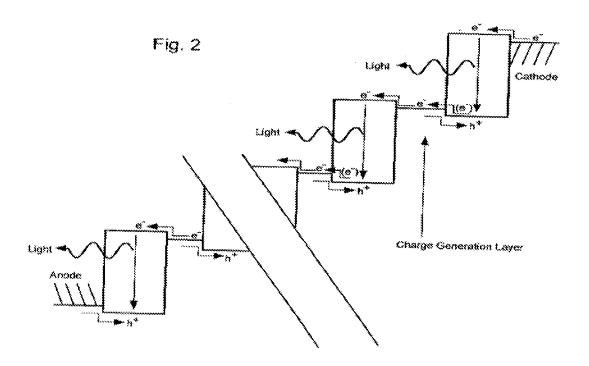
Claims 9-20 and 32-47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kido et al., USP App. Pub. No. 2003/0189401 A1, published October 9, 2003 (hereinafter referred to as "Kido") in view of Nakaya et al., USP App. Pub. No. 2004/0234814 A1, published November 25, 2004 (hereinafter referred to as "Nakaya").

Regarding claim 9, Kido discloses a light emitting element comprising: a first electrode and a second electrode (e.g., Fig. 2 above, anode and cathode); a first layer generating holes ([0028]; "it is desirable for the charge generation layer to include a laminated

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and/or a mixed layer including an organic compound having...a hole transporting property [i.e., hole generating layer]...and an inorganic...material"); a third layer containing a light emitting material (e.g., Figure 2, light emitting layer); and a fourth layer generating electrons (e.g., [0041]; "an electron injection layer having a mixture including an organic compound and a metal functioning as an electron donating dopant").



Regarding claim 13, Kido discloses a light emitting element comprising: a first electrode and a second electrode (e.g., Fig. 2 above, cathode and anode); a first layer containing a P-type semiconductor ([0028]; "it is desirable for the charge generation layer to include a laminated and/or a mixed layer including an organic compound having...a hole transporting property [i.e., P-type semiconductor]...and an inorganic...material"); a third layer containing a light emitting material (e.g., Figure 2, light emitting layer); and a fourth layer

containing an N-type semiconductor (e.g., [0041]; "an electron injection layer having a mixture including an organic compound and a metal functioning as an electron donating dopant [i.e., N-type semiconductor]").

Regarding claim 34, Kido discloses a light emitting element comprising: a first electrode over a substrate (e.g., Fig. 2 above, anode over substrate, [0057]); a first layer generating holes over and in contact with the first electrode ([0028]; "it is desirable for the charge generation layer to include a laminated and/or a mixed layer including an organic compound having...a hole transporting property [i.e., hole generating layer]...and an inorganic...material [i.e., which accepts the electrons of the organic material]"); a third layer containing a light emitting material over the first layer (e.g., Figure 2, light emitting layer); a fourth layer generating electrons over the third layer (e.g., [0041]; "an electron injection layer having a mixture including an organic compound and a metal functioning as an electron donating dopant"); and a second electrode (cathode).

Regarding claim 39, Kido discloses a light emitting element comprising: a first electrode over a substrate (e.g., Fig. 2 above, anode over substrate, [0057]); a first layer containing a P-type semiconductor over and in contact with the first electrode ([0028]; "it is desirable for the charge generation layer to include a laminated and/or a mixed layer including an organic compound having...a hole transporting property [i.e., P-type semiconductor]...and an inorganic...material"; Note: each of the layers is either directly or indirectly contacting the other layers of the device because there are no gaps between the layers); a third layer containing a light emitting material over the first layer (e.g., Figure 2, light emitting layer); a fourth layer containing an N-type semiconductor over the third layer (e.g., [0041]; "an electron injection

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layer having a mixture including an organic compound and a metal functioning as an electron donating dopant [i.e., N-type semiconductor]"), a second electrode (e.g., cathode).

Regarding claims 9, 13, 34 and 39, Kido fails to teach a second hole generating layer in contact with the cathode. However, in the same field of endeavor of EL displays, Nakaya teaches a second layer generating holes (and containing a P-type semiconductor) ([0240-0241]), wherein the first layer is in direct contact with the first electrode (layer 5 in direct contact with electrode 2, Figure 2), the second layer is in direct contact with the second electrode ([0240-0241]), the third layer is provided between the first electrode and the second electrode with the first layer and the second layer respectively therebetween (layers 3a and 3b, Figure 2), and the fourth layer is provided between the third layer and the second layer (layer 6, Figure 2 and [0240-0241]).

Figure 2

B

6
3b
3c

It would have been obvious to one of ordinary skill in the art at the time the invention was made to utilize a second hole injection layer on the cathode side of the device, as taught by Nakaya, because said layer can serve as a buffer layer between the light emitting layer and the cathode, thereby lowering the driving voltage of the device (Nakaya; [0241]).

Regarding claims 10, 18, 35 and 44, Kido and Nakaya disclose the inventions as explained above regarding claims 9, 13, 34 and 39 respectively, and Kido further discloses **the**

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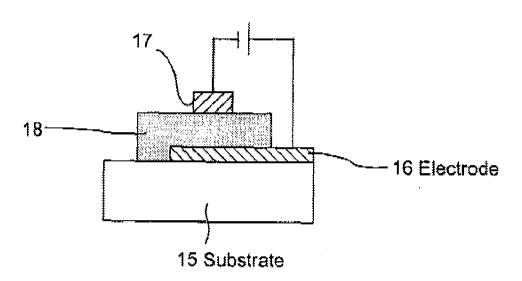
thickness of each of the first layer and the second layer is 30 nm to 1 µm (e.g., [0052]; "a hole injection layer including an electron accepting compound and having a thickness of not more than 30 nm [i.e., including 30 nm, which is within the claimed range]"; see also Figure 2, there are two hole transporting layers, one on either side of the light emitting layer).

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Regarding claims 11, 19, 36 and 45, Kido and Nakaya disclose the inventions as explained above regarding claims 9, 13, 34 and 39 respectively, and Kido further discloses the thickness of the second layer is 50% to 150% of the thickness of the first layer, and the thickness of the first layer is 50% to 150% of the thickness of the second layer (e.g., [0052]; "a hole injection layer including an electron accepting compound and having a thickness of not more than 30 nm [i.e., including 30 nm, which is within the claimed range]"; see also Figure 2, there are two hole transporting layers, one on either side of the light emitting layer, and they are each of the thickness not more than 30 nm).

Regarding claims 12, 20, 37 and 46, Kido and Nakaya disclose the inventions as explained above regarding claims 9, 13, 34 and 39 respectively, and Kido further discloses t voltage is applied so as to make the light emitting element emit light, the electrode applied with higher potential is the first electrode, and the electrode applied with lower potential is the second electrode (e.g., Figure 34 below, higher potential applied to first electrode, lower potential applied to second electrode, denoted by conventional circuitry).

Fig. 34



Regarding claims 14 and 40, Kido and Nakaya disclose the inventions as explained above regarding claims 13 and 39 respectively, and Kido further discloses the inorganic material (the P-type semiconductor; the material which accepts electrons) is a metal oxide (e.g., [0033]; "the inorganic material can be a metal oxide").

Regarding claims 15 and 41, Kido and Nakaya disclose the inventions as explained above regarding claims 13 and 39 respectively, and Kido further discloses the metal oxide (the P-type semiconductor) is one or more compounds selected from the group consisting of vanadium oxide, molybdenum oxide, cobalt oxide, and nickel oxide, zinc oxide, indium oxide, tin oxide, antimony oxide, and tungsten oxide (e.g., [0035]; "the metal oxide can be vandium pentaoxide").

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Regarding claims 16 and 42, Kido and Nakaya disclose the inventions as explained above regarding claims 13 and 39 respectively, and Kido further discloses the N-type semiconductor is a metal oxide (e.g., [0041]; "an electron injection layer [i.e., N-type semiconductor] having...a metal functioning as an electron donating dopant" and [0033]; "the inorganic material [i.e., the metal included in any of the charge generation layers] can be a metal oxide").

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Regarding claims 17 and 43, Kido and Nakaya disclose the inventions as explained above regarding claims 13 and 39 respectively, and Kido further discloses the N-type semiconductor is one or more compounds selected from the group consisting of zinc oxide, zinc sulfide, zinc selenide, and titanium oxide (e.g., [0033]; "the inorganic material [i.e., the metal in a charge generation layer] can be a metal oxide" and [0047]; "metal to include at least one selected from...titanium").

Regarding claims 32, 33, 38 and 47, Kido and Nakaya teach the inventions as explained above regarding claims 9, 13, 34 and 39 respectively, and Nakaya further teaches the light emitting element is incorporated in one selected from the group consisting of a television, a mobile phone, a computer, and a game machine ([0227]).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to utilize the light emitting device of Kido in a display device such as those listed in Nakaya, because OLEDs are suitable light emitting sources for the display devices listed in Nakaya.

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Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to MARY ELLEN BOWMAN whose telephone number is (571)

270-5383. The examiner can normally be reached on Monday-Thursday, 7:30 a.m.-6:00 p.m.

EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Nimesh Patel can be reached on (571) 272-2457. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

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information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/M. B./

Examiner, Art Unit 2879

/NIMESHKUMAR D. PATEL/

Supervisory Patent Examiner, Art Unit 2879